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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. .... 09/879,335 -  
Filing Date ..... June 11, 2001 -  
Inventor ..... Vishnu K. Agarwal, et al  
Assignee ..... Micron Technology, Inc.  
Group Art Unit ..... 2813  
Examiner ..... Y. Huynh  
Attorney's Docket No. .... MI22-1568  
Title: Capacitor Forming Methods with Barrier Layers to Threshold Voltage Shift  
Inducing Material

**PRELIMINARY AMENDMENT TO ACCOMPANY RCE FILING**

To: Box RCE  
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Washington, D.C. 20231

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TC-2800 MAIL ROOM

**AMENDMENTS**

**In the Claims**

Please add new claims 58-65 in accordance with 37 C.F.R. 1.121(c)(1)(i).

- 58. The method of claim 1 wherein the barrier layer is formed on the insulation layer.
- 59. The method of claim 1 further comprising providing  $V_t$  shift inducing material over the insulation layer.
- 60. The method of claim 16 wherein the barrier layer is formed on the insulation layer.
- 61. The method of claim 22 wherein the barrier layer is formed on the substrate.

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